



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	57mΩ @ V _{GS} = 10V	5.8A
30V	112mΩ @ V _{GS} = 4.5V	2.5A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- **Power Management Functions**
- **Boost Application**
- **Analog Switch**

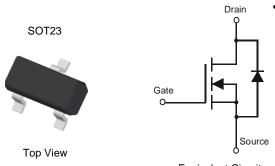
Features

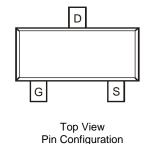
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN3112SQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208(63)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)





Equivalent Circuit

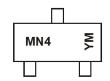
Ordering Information (Note 4)

Ī	Part Number	Qualification	Case	Packaging		
	DMN3112SQ-7	Automotive	SOT23	3000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



MN4 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: I = 2021)M = Month (ex: 9 = September)

Data Cada Kay

Date Code Key											
Year	2014	 2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	В	 ı	J	K	L	М	N	0	Р	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		VDSS	30	V
Gate-Source Voltage		Vgss	±20	V
Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	lo	5.8 4.2	А
Drain Current (Note 5)	Pulsed	I _{DM}	20	A
Body-Diode Continuous Current (Note 5)		Is	2.0	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	1.4	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	Reja	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)	OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BVDSS	30		_	V	Vgs = 0V, ID = 250µA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	800	nA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	±80 ±800	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _G S(TH)	1.3	1.9	2.2	V	V _{DS} = V _{GS} , I _D = 250μA	
Static Drain-Source On-Resistance	RDS(ON)	_	47 92	57 112	mΩ	V _{GS} = 10V, I _D = 5.8A V _{GS} = 4.5V, I _D = 4.2A	
Forward Transconductance	Yfs	_	4.7	_	S	V _{DS} = 5V, I _D = 4.2A	
Source-Drain Diode Forward Voltage	VsD	_	0.78	1.1	V	Vgs = 0V, Is = 2.0A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	_	268	_	pF	., -,,,,	
Output Capacitance	Coss	_	73	_	pF	V _{DS} = 5V, V _{GS} = 0V - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	50	_	pF] = 1.0IVII IZ	

Notes:

- 5. Device mounted on FR-4 PCB. t ≤5 sec.
 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.



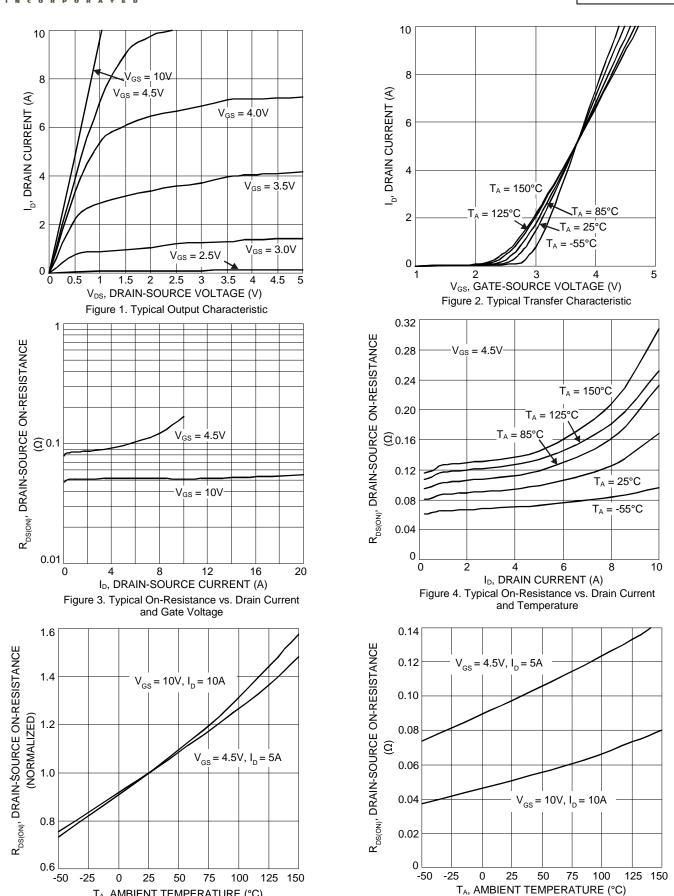


Figure 6. On-Resistance Variation with Temperature Figure 5. On-Resistance Variation with Temperature

TA, AMBIENT TEMPERATURE (°C)



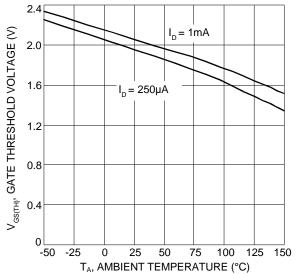
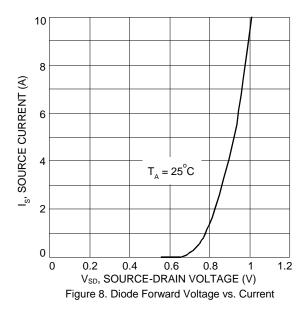
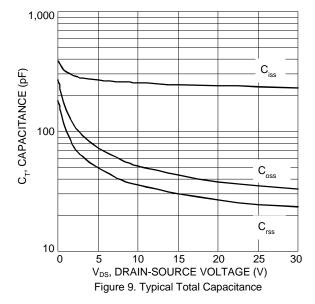


Figure 7. Gate Threshold Variation vs. Ambient Temperature





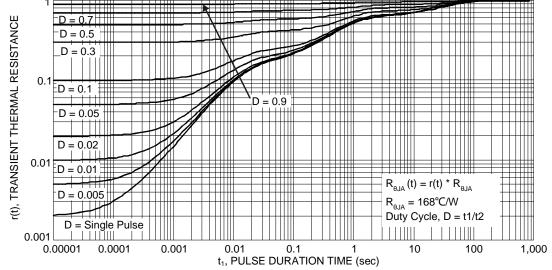


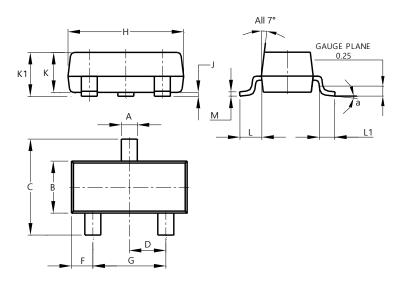
Figure 10. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

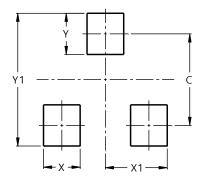


	so	T23		
Dim	Min	Max	Тур	
Α	0.37	0.51	0.40	
В	1.20	1.40	1.30	
С	2.30	2.50	2.40	
D	0.89	1.03	0.915	
F	0.45	0.60	0.535	
G	1.78	2.05	1.83	
Н	2.80	3.00	2.90	
J	0.013	0.10	0.05	
K	0.890	1.00	0.975	
K1	0.903	1.10	1.025	
L	0.45	0.61	0.55	
L1	0.25	0.55	0.40	
M	0.085	0.150	0.110	
а	0°	8°		
All	Dimens	ions in	mm	

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

August 2021



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